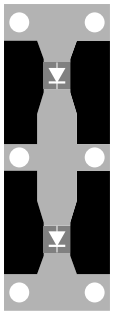
Silicon Dual Flip Chip Schottky Diode

BAT 14-077D

Preliminary Data Sheet

- Dual Schottky medium Barrier Mixer Diode
- For W-band application up to 80 GHz



EHT09236

ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration			Package
BAT 14-077D	–	Q62702-D1354	–	–	–	FLIP CHIP

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	3	V
Forward current	I_F	25	mA
Total power dissipation (T_S = 25 °C)	P_{tot}	20	mW
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	– 40 … + 150	°C
Storage temperature	T_{stg}	– 55 … + 150	°C

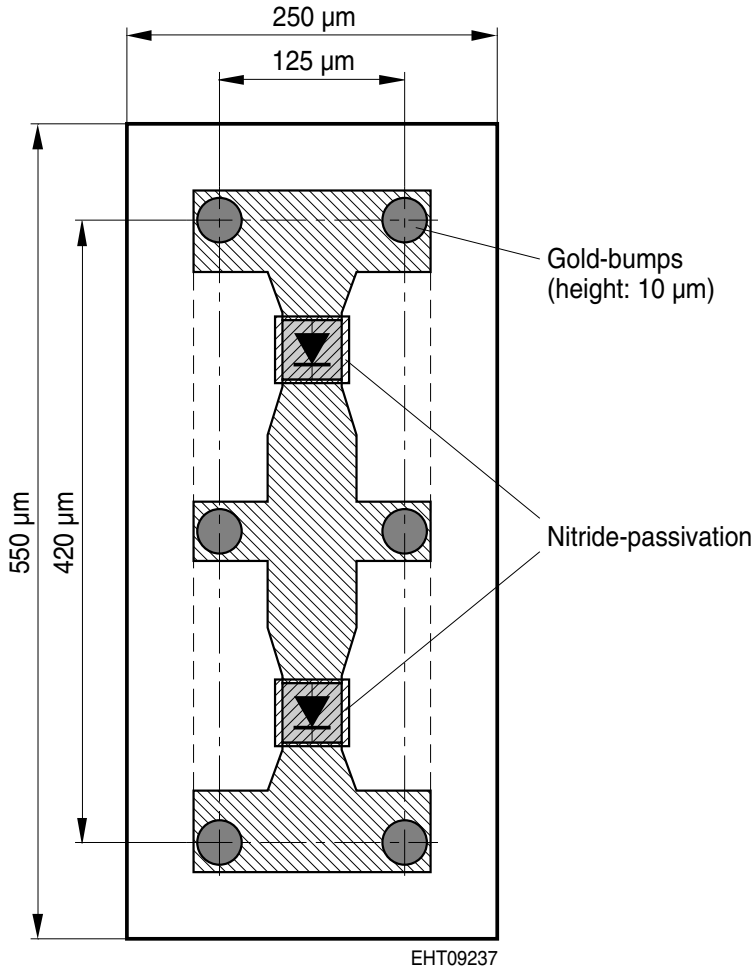
Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Limit Values			Unit	Test Conditions
		min.	typ.	max.		
DC Characteristics						
Breakdown voltage	$V_{(BR)}$	3	–	–	V	$I_{(BR)}$ = 100 µA
Forward voltage	V_F	–	0.4	0.5	V	I_F = 100 µA
AC Characteristics						
Diode capacitance[1)]	C_T	–	30	–	fF	V_R = 0 V
Forward resistance	R_F	–	7	10	Ω	I_F = 10 mA

1) Simulated values test conditions t.b.f.

Chip Layout

FLIP CHIP



Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book “Package Information”.

Dimensions in mm